
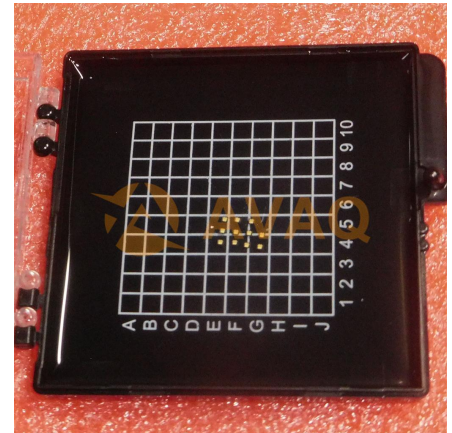


Trans RF FET N-CH 40V 2.5A 4-Pin Chip

Manufacturer:	Qorvo, Inc
Package/Case:	SMD
Product Type:	Thyristors
RoHS:	RoHS Compliant/Lead free 
Lifecycle:	Active



Images are for reference only

[Inquiry](#)

General Description

Qorvo's TGF2023-2-02 is a discrete 2.5 mm GaN on SiC HEMT which operates from DC to 18 GHz.

The TGF2023-2-02 typically provides 40.1 dBm of saturated output power with power gain of 21 dB at 3 GHz. The maximum power added efficiency is 73.3% which makes the TGF2023-2-02 appropriate for high efficiency applications.

The part is lead-free and RoHS compliant.

Key Features

Frequency range: DC to 18 GHz

40.1 dBm nominal Psat at 3 GHz

73.3% maximum PAE

21 dB nominal power gain

Bias: VD = 12 to 32 V, IDQ= 50 - 250 mA

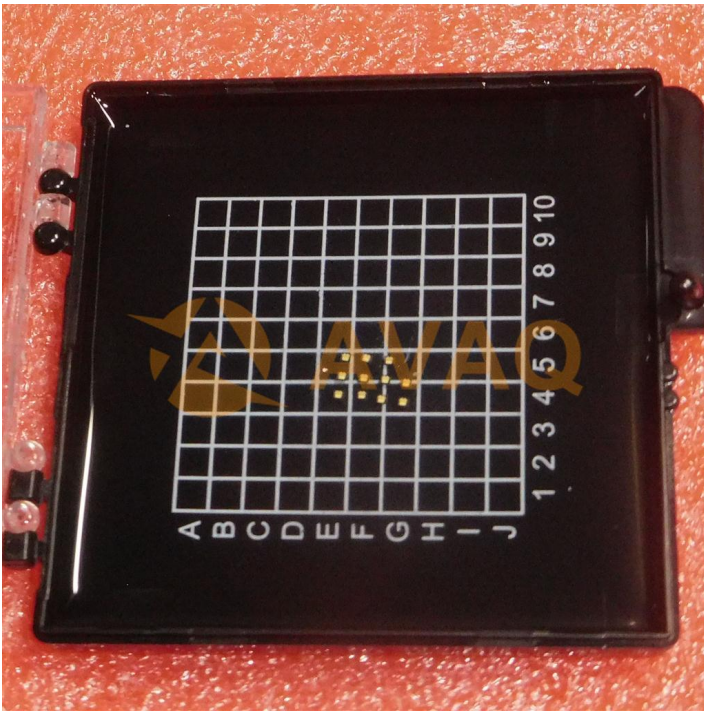
Chip dimensions: 0.82 x 0.92 x 0.10 mm

Application

Broadband Wireless

Military

Space



Recommended For You

TGF2977-SM

Qorvo, Inc

SMD

TGF2023-2-10

Qorvo, Inc

SMD

T2G6000528-Q3

Qorvo, Inc

SMD

QPD1010

Qorvo, Inc

QFN

QPD1003

Qorvo, Inc

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QPD1008L

Qorvo, Inc

SMD